

廖洺漢

著作目錄

期刊論文

1. C. Liu, P.-G. Chen, M.-J. Xie, S.-N. Liu, J.-W. Lee, S.-J. Huang, S. Liu, Y.-S. Chen, H.-Y. Lee, M.-H. Liao, P.-S. Chen, and M.-H. Lee (2016, Mar). Simulation-based study of negative capacitance double gate tunnel field effect transistor with ferroelectric gate stack. *Japanese Journal of Appl. Phys*, Vol. 55, p. 04EB08, 2016.
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3. M.-H. Liao, C.-H. Yeh, C.-C. Lee, and C.-P. Wang (2016, Mar). The investigation of the diameter dimension effect on the Si nano-tube transistors. *AIP Advances*, Vol. 6, p. 035021, 2016. 本人為第一作者、通訊作者。
4. C. C. Lee, C.-P. Hsieh, P.-C. Huang, S.-W. Cheng, and M.-H. Liao (2016, Jan). STI Geometric Influence of a Recessed Surface on Array-type Arrangements of Nano-scaled Devices Strained by CESL and Ge-based Stressors. *Thin Solid Films*, 1.
5. C. C. Lee, S. W. Cheng, C. P. Hsieh, M.-H. Liao, and Y. H. Guo (2015, Oct). Comprehensive Investigation on Array-Type Dummy Active Diffused Region and Gate Geometries Using Narrow NMOSFETs with SiC S/D Stressors. *International Journal of Nanotechnology*, 2015.
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8. M.-H. Liao and P.-G. Chen (2015, Aug). The dependency of different stress-level SiN capping films and the optimization of D-SMT process for the device performance booster in Ge n-FinFETs. *Appl. Phys. Lett.*, Vol. 107, p. 072111. MOST 103-2221-E-002-215-MY3. 本人為第一作者、通訊作者。The partly

experimental process support from NDL is also highly appreciated. The support from the Big League Program with TSMC is also highly appreciated.

9. M.-H. Liao and C. Lien (2015, May). The comprehensive study and the reduction of contact resistivity on the n-InGaAs MIS contact system with different inserted insulators. *AIP Advances*, Vol. 5, p. 057117, 2015.. 本人為第一作者、通訊作者.
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11. M.-H. Liao and P.-G. Chen (2015, Apr). The demonstration of dislocation-stress memorization technique stressor on Si n-FinFETs. *IEEE Transactions on Nanotechnology*, Vol. 14(4), p. 657, 2015.. MOST 102-2218-E-002-003. 本人為第一作者、通訊作者.
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21. Li-Tien Huang, Ming-Lun Chang, Jih-Jie Huang, Chin-Lung Kuo, Hsin-Chih Lin, Ming-Han Liao, Min-Hung Lee and Miin-Jang Chen (2012, Dec). Effect of hydrogen participation on the improvement in electrical characteristics of HfO₂ gate dielectrics by post-deposition remote N₂, N₂/H₂, and NH₃ plasma treatments. *J. Phys. D: Appl. Phys.*, 055103. 本人為通訊作者.
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研討會論文

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3. M.-H. Liao, P. G. Chen, S. C. Huang, S. C. Kao, C. X. Hung, K. H. Liu, C. Lien,

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4. M.-H. Liao, S. C. Huang, C. Y. Liu, P. G. Chen, S. C. Kao, and C. Lien (2014, Jun). The demonstration of colossal magneto-capacitance and “negative” capacitance effect with the promising characteristics of Jg-EOT and transistor’s performance on Ge (100) n-FETs by the novel magnetic gate stack scheme design. 2014 Symposium on VLSI Technology (VLSI-technology), 美國夏威夷. 本人為第一作者、通訊作者. 2014 Symposium on VLSI Technology.